

2SD662, 2SD662B

Silicon NPN epitaxial planer type

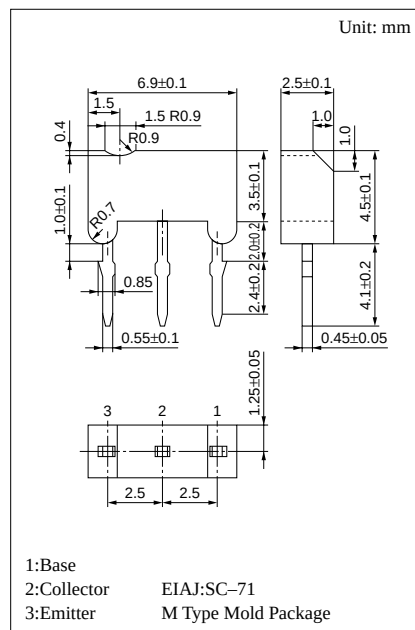
For high breakdown voltage general amplification

Features

- High collector to emitter voltage V_{CEO} .
- High transition frequency f_T .
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	250	V
2SD662B		400	
Collector to emitter voltage	V_{CEO}	200	V
2SD662B		400	
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	100	mA
Collector current	I_C	70	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

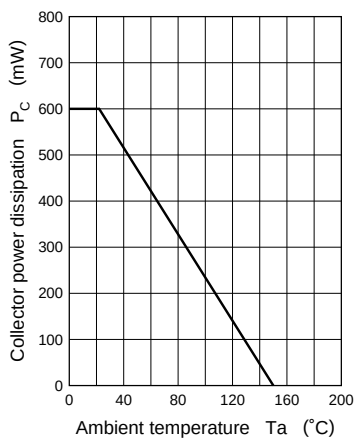
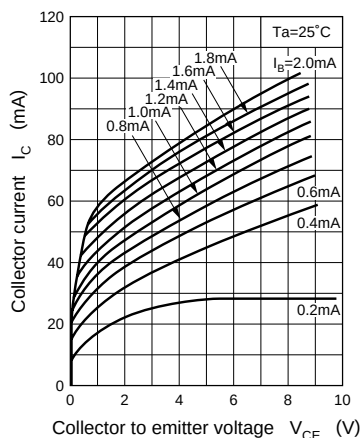
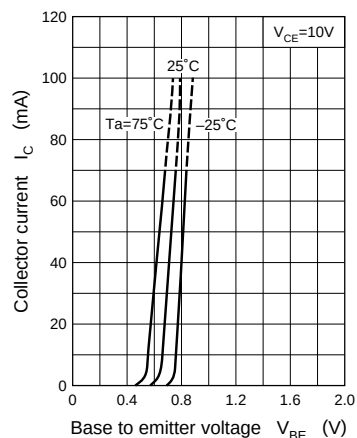
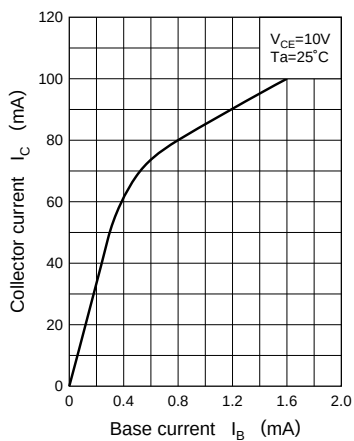
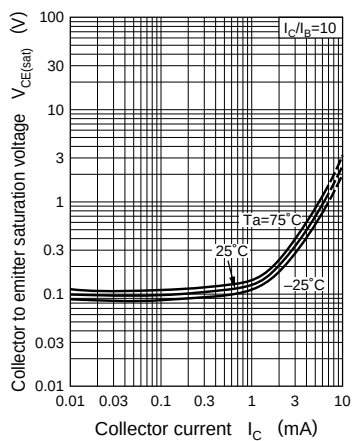
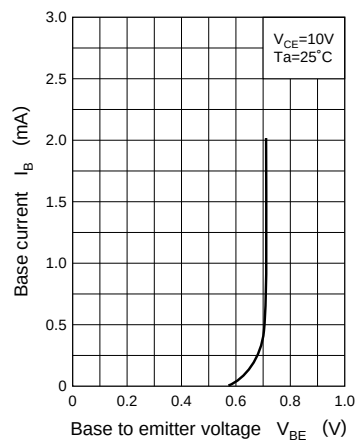
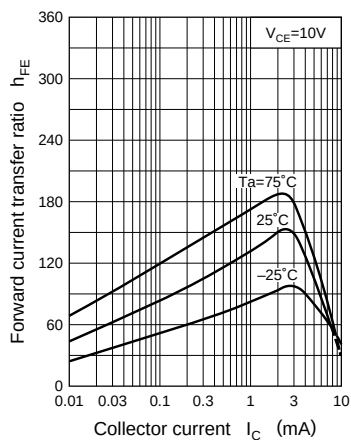
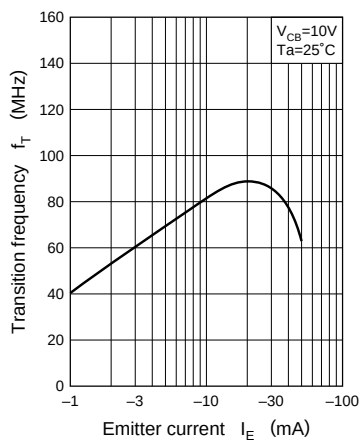


Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = 100\text{V}, I_B = 0$			2	μA
Collector to emitter voltage	V_{CEO}	$I_C = 100\mu\text{A}, I_B = 0$	200			V
			400			
Emitter to base voltage	V_{EBO}	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 10\text{V}, I_C = 5\text{mA}$	30		220	
			30		150	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CB} = 10\text{V}, I_E = -10\text{mA}, f = 200\text{MHz}$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		5	10	pF

* h_{FE} Rank classification

Rank	P	Q	R
h_{FE}	30 ~ 100	60 ~ 150	100 ~ 220

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $I_C - I_B$  $V_{CE(sat)} - I_C$  $I_B - V_{BE}$  $h_{FE} - I_C$  $f_T - I_E$  $I_{CBO} - T_a$ 